

MC74HCT14A

Hex Schmitt-Trigger Inverter with LSTTL Compatible Inputs

High-Performance Silicon-Gate CMOS

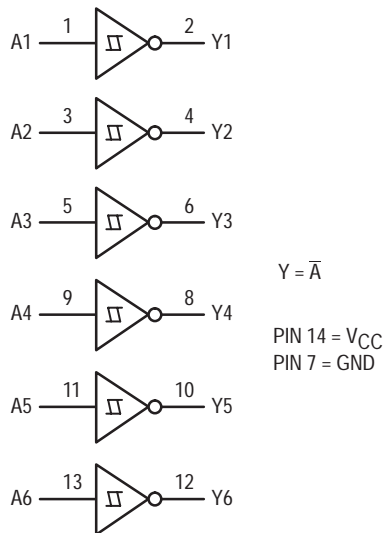
The MC74HCT14A may be used as a level converter for interfacing TTL or NMOS outputs to high-speed CMOS inputs.

The HCT14A is identical in pinout to the LS14.

The HCT14A is useful to “square up” slow input rise and fall times. Due to the hysteresis voltage of the Schmitt trigger, the HCT14A finds applications in noisy environments.

- Output Drive Capability: 10 LSTTL Loads
- TTL/NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μ A
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 72 FETs or 18 Equivalent Gates

LOGIC DIAGRAM



FUNCTION TABLE

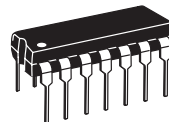
Input A	Output Y
L	H
H	L



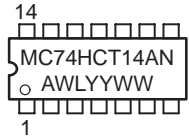
ON Semiconductor

<http://onsemi.com>

MARKING DIAGRAMS



PDIP-14
N SUFFIX
CASE 646

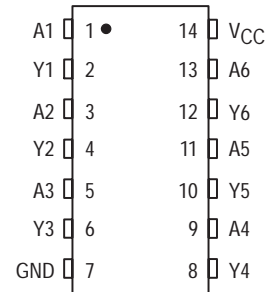


SOIC-14
D SUFFIX
CASE 751A



A = Assembly Location
WL or L = Wafer Lot
YY or Y = Year
WW or W = Work Week

PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping
MC74HCT14AN	PDIP-14	2000 / Box
MC74HCT14AD	SOIC-14	55 / Rail
MC74HCT14ADR2	SOIC-14	2500 / Reel

MC74HCT14A

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
I _{in}	DC Input Current, per Pin	± 20	mA
I _{out}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 50	mA
P _D	Power Dissipation in Still Air, Plastic DIP† SOIC Package†	750 500	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C °C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

*Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions

†Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	—	*	ns

*No Limit when V_{in} ≈ 50% V_{CC}, I_{CC} > 1 mA.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} Volts	Temperature Limit						Unit
				- 55 to 25°C		≤ 85°C		≤ 125°C		
				Min	Max	Min	Max	Min	Max	
V _{T+} max	Maximum Positive-Going Input Threshold Voltage	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	4.5 5.5		1.9 2.1		1.9 2.1		1.9 2.1	V
V _{T+} min	Minimum Positive-Going Input Threshold Voltage	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	4.5 5.5	1.2 1.4		1.2 1.4		1.2 1.4		V
V _{T-} max	Maximum Positive-Going Input Threshold Voltage	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	4.5 5.5		1.2 1.4		1.2 1.4		1.2 1.4	
V _{T-} min	Minimum Positive-Going Input Threshold Voltage	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	4.5 5.5	0.5 0.6		0.5 0.6		0.5 0.6		
V _H max	Maximum Hysteresis Voltage	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	4.5 5.5		1.4 1.5		1.4 1.5		1.4 1.5	
V _H min	Minimum Hysteresis Voltage	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	4.5 5.5	0.4 0.4		0.4 0.4		0.4 0.4		
V _{OH}	Minimum High-Level Output Voltage	V _{in} < V _{T-} min I _{out} ≤ 20 μA	4.5 5.5	4.4 5.4		4.4 5.4		4.4 5.4		V
		V _{in} < V _{T-} min I _{out} ≤ 4.0 mA	4.5	3.98		3.84		3.7		

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).
(continued)

MC74HCT14A

DC CHARACTERISTICS (Voltages Referenced to GND) – continued

Symbol	Parameter	Test Conditions	V _{CC} Volts	Temperature Limit						Unit
				– 55 to 25°C		≤ 85°C		≤ 125°C		
				Min	Max	Min	Max	Min	Max	
V _{OL}	Maximum Low-Level Output Voltage	V _{in} ≥ V _T +max I _{out} ≤ 20 μA	4.5 5.5		0.1 0.1		0.1 0.1		0.1 0.1	V
		V _{in} ≥ V _T +max I _{out} ≤ 4.0 mA	4.5		0.26		0.33		0.4	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	5.5		± 0.1		± 1.0		± 1.0	μA
I _{CC}	Maximum Quiescent Supply Current (per package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	5.5		1.0		10		40	μA
ΔI _{CC}	Additional Quiescent Supply Current	V _{in} = 2.4 V, Any One Input V _{in} = V _{CC} or GND, Other Inputs I _{out} = 0 μA	5.5		≥ – 55°C		25°C to 125°C			mA
					2.9	2.4				

AC CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6.0 ns)

Symbol	Parameter	Test Conditions		Guaranteed Limit						Unit
				– 55 to 25°C		≤ 85°C		≤ 125°C		
				Min	Max	Min	Max	Min	Max	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (L to H)	V _{CC} = 5.0 V ± 10% C _L = 50 pF, Input t _r = t _f = 6.0 ns	Fig. 1 & 2		32		40		48	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time. Any Output	V _{CC} = 5.0 V ± 10% C _L = 50 pF, Input t _r = t _f = 6.0 ns	Fig. 1 & 2		15		19		22	ns

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

C _{PD}	Power Dissipation Capacitance (Per Inverter)*	Typical @ 25°C, V _{CC} = 5.0 V		pF
		32		

* Used to determine the no-load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

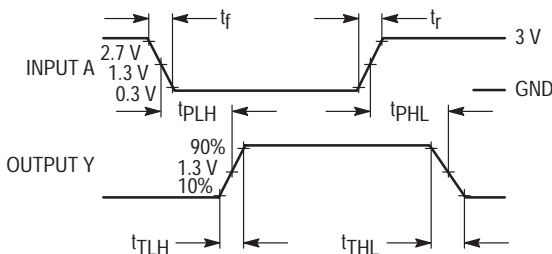
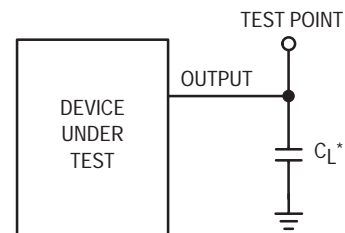


Figure 1. Switching Waveforms



*Includes all probe and jig capacitance

Figure 2. Test Circuit